

Nico Kaiser

List of Publications by Year in descending order

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Version: 2024-02-01

11
papers

191
citations

1307594

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h-index

1372567

10
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docs citations

11
times ranked

219
citing authors

#	ARTICLE	IF	CITATIONS
1	Enhanced Conductivity and Microstructure in Highly Textured TiN _{1-x} /Al ₂ O ₃ Thin Films. ACS Omega, 2022, 7, 2041-2048.	3.5	1
2	Defect-Stabilized Substoichiometric Polymorphs of Hafnium Oxide with Semiconducting Properties. ACS Applied Materials & Interfaces, 2022, 14, 1290-1303.	8.0	27
3	Defect-Induced Phase Transition in Hafnium Oxide Thin Films: Comparing Heavy Ion Irradiation and Oxygen-Engineering Effects. IEEE Transactions on Nuclear Science, 2021, 68, 1542-1547.	2.0	12
4	Tailoring the Switching Dynamics in Yttrium Oxide-Based RRAM Devices by Oxygen Engineering: From Digital to Multi-Level Quantization toward Analog Switching. Advanced Electronic Materials, 2020, 6, 2000439.	5.1	20
5	Enhanced thermal stability of yttrium oxide-based RRAM devices with inhomogeneous Schottky-barrier. Applied Physics Letters, 2020, 117, .	3.3	26
6	Role of Oxygen Defects in Conductive-Filament Formation in Y ₂ O ₃ -Based Analog RRAM Devices as Revealed by Fluctuation Spectroscopy. Physical Review Applied, 2020, 14, .	3.8	15
7	Machine Learning Assisted Pattern Matching: Insight into Oxide Electronic Device Performance by Phase Determination in 4D-STEM Datasets. Microscopy and Microanalysis, 2020, 26, 1908-1909.	0.4	3
8	Heavy Ion Irradiation Effects on Structural and Ferroelectric Properties of HfO ₂ Films. , 2020, , .		3
9	Forming-Free Grain Boundary Engineered Hafnium Oxide Resistive Random Access Memory Devices. Advanced Electronic Materials, 2019, 5, 1900484.	5.1	57
10	Correlation of Structural Modifications by Multiscale Phase Mapping in Filamentary Type HfO ₂ -based RRAM: Towards a Component Specific in situ TEM Investigation. Microscopy and Microanalysis, 2019, 25, 1842-1843.	0.4	1
11	Analysis and simulation of the multiple resistive switching modes occurring in HfO _x -based resistive random access memories using memdiodes. Journal of Applied Physics, 2019, 125, .	2.5	26